

ON Semiconductor®

FDD8445-F085

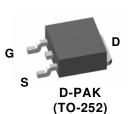
N-Channel PowerTrench® MOSFET 40V, 50A, 6.7m Ω Features

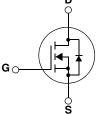
- Typ $R_{DS(on)} = 6.7 \text{m}\Omega$ at $V_{GS} = 10 \text{V}$, $I_D = 50 \text{A}$
- Typ $Q_{q(10)} = 45$ nC at $V_{GS} = 10V$, $I_D = 50$ A
- Low Miller Charge
- Low Qrr Body Diode
- UIS Capability (Single Pulse/ Repetitive Pulse)
- RoHS Compliant
- Qualified to AEC Q101

Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Transmission
- Distributed Power Architecture and VRMs
- Primary Switch for 12V Systems







MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	±20	V
	Drain Current Continuous (V _{GS} = 10V)	50	Α
ID	Pulsed	Figure 4	_ A
E _{AS}	Single Pulse Avalanche Energy (Note 1)	144	mJ
D	Power Dissipation	79	W
P_D	Derate above 25°C	0.53	W/°C
T_J , T_{STG}	Operating and Storage Temperature	-55 to +175	°C
$R_{\theta JC}$	Thermal Resistance Junction to Case	1.9	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, 1in ² copper pad area	52	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8445	FDD8445-F085	TO-252AA	13"	12mm	2500 units

Notes:

1: Starting T_J = 25°C, L = 0.18mH, I_{AS} = 40A 2: A suffix as "...F085P" has been temporarily introduced in order to manage a double source strategy as ON Semiconductor has officially announced in Aug 2014.

Units

Max

Тур

Electrical Characteristics $T_A = 25^{\circ}C$ unless otherwise noted

Parameter

Off Characteristics							
B _{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} =$	0V	40	-	-	V
1	Zero Gate Voltage Drain Current	$V_{DS} = 32V$,		-	-	1	μА
IDSS		$V_{GS} = 0V$	$T_A = 150^{\circ}C$	-	-	250	
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20V$		ı	-	±100	nA

Test Conditions

Min

On Characteristics

Symbol

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2	2.8	4	٧
		$I_D = 50A, V_{GS} = 10V$	-	6.7	8.7	
r _{DS(on)}	Drain to Source On Resistance	$I_D = 50A, V_{GS} = 10V$ $T_J = 175^{\circ}C$	-	12.5	16.3	mΩ

Dynamic Characteristics

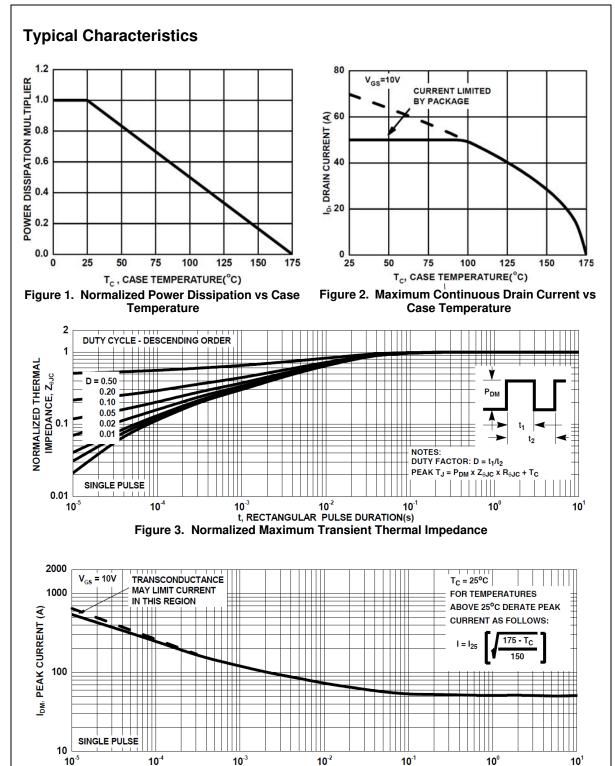
C _{iss}	Input Capacitance	- V _{DS} = 25V, V _{GS} = 0V, - f = 1MHz		-	3040	4050	рF
C _{oss}	Output Capacitance			-	295	390	рF
C _{rss}	Reverse Transfer Capacitance			-	178	270	pF
R _G	Gate Resistance	f = 1MHz		-	1.7	-	Ω
$Q_{g(TOT)}$	Total Gate Charge at 10V	V _{GS} = 0 to 10V	V _{DD} = 20V I _D = 50A	-	45	59	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to $2V$			5.8	7.6	nC
Q _{gs}	Gate to Source Gate Charge			-	12.5	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	10.5	-	nC

Switching Characteristics

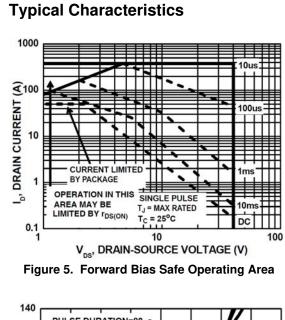
t _{on}	Turn-On Time	$V_{DD} = 20V, I_D = 50A$ $V_{GS} = 10V, R_{GS} = 2\Omega$	-	-	138	ns
t _{d(on)}	Turn-On Delay Time		-	10	-	ns
t _r	Rise Time		-	82	-	ns
t _{d(off)}	Turn-Off Delay Time		-	26	-	ns
t _f	Fall Time		-	9.6	-	ns
t _{off}	Turn-Off Time		-	-	53	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 50A$	-	-	1.25	V
	Source to Drain Diode Voltage	$I_{SD} = 25A$	-	-	1.0	
t _{rr}	Reverse Recovery Time	I 504 dl (dt 1004/	-	-	39	ns
Q_{rr}	Reverse Recovery Charge	$I_{SD} = 50A$, $dI_{SD}/dt = 100A/\mu s$	-	-	38	nC



t, RECTANGULAR PULSE DURATION(s)
Figure 4. Peak Current Capability



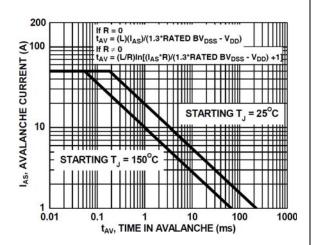
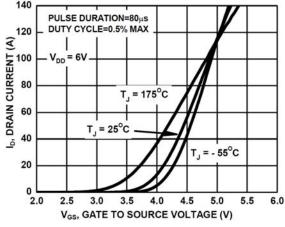


Figure 6. Unclamped Inductive Switching Capability



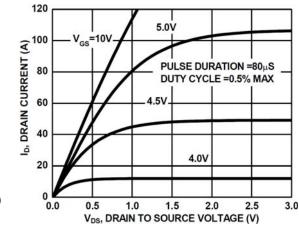
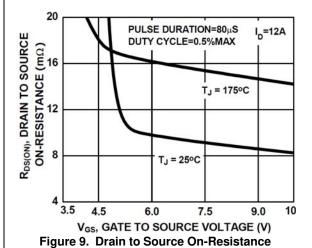


Figure 7. Transfer Characteristics

Figure 8. Saturation Characteristics



Variation vs Gate to Source Voltage

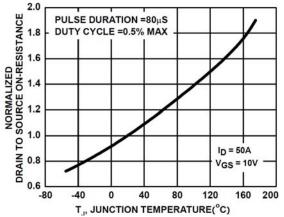


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics

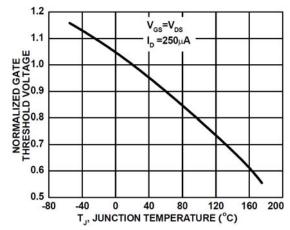


Figure 11. Normalized Gate Threshold Voltage vs **Junction Temperature**

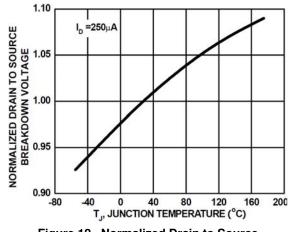


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

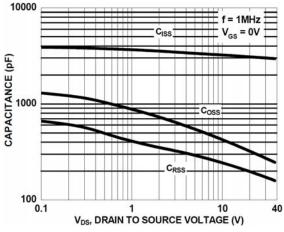


Figure 13. Capacitance vs Drain to Source Voltage

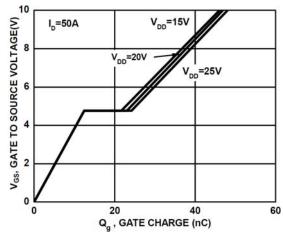


Figure 14. Gate Charge vs Gate to Source Voltage

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and h

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative